



Micro Commercial Components 20736 Marilla Street Chatsworth CA 91311

Phone: (818) 701-4933 Fax: (818) 701-4939 **SIL2308**

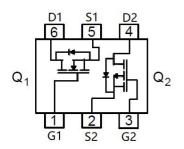
Features

- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- · Moisture Sensitivity Level 1
- Low Input/Output Leakage
- Marking Code: 2038

Maximum Ratings @ 25°C Unless Otherwise Specified

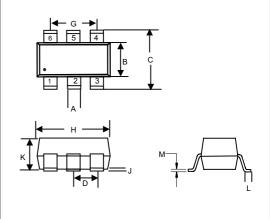
Symbol	Parameter		Rating	Unit
V_{DS}	Drain-source Voltage	N-Channel	20	V
		P-Channel	-20	V
I _D	Drain Current-Continuous	N-Channel	5	А
		P-Channel	-4	A
V_{GS}	Gate-source Voltage	N-Channel	±8	V
		P-Channel	±12	V
R _{⊕JA}	Thermal Resistance Junction to Ambient		277	°C/W
T_J	Operating Junction Temperature		-55 to +150	$^{\circ}\mathbb{C}$
T _{STG}	Storage Temperature		-55 to +150	$^{\circ}\!\mathbb{C}$

Equivalent Circuit



Dual N&P-Channel MOSFET

SOT23-6L



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
Α	.012	.020	0.30	0.50	
В	.051	.070	1.30	1.80	
С	.087	.126	2.20	3.20	
D	.037		0.95BSC		
G	.074		1.90BSC		
Н	.106	.122	2.70	3.10	
J	.002	.006	0.05	0.15	
K	.035	.051	0.90	1.30	
Ĺ	.012	.024	0.30	0.60	
M	.003	.008	0.08	0.22	



Electrical characteristics - N-Channel Q1 (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Static Characteristics	·					
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V,V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V			±0.1	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	1	V
Drain-source on-resistance		V _{GS} =4.5V, I _D =4.5A			38	mΩ
	R _{DS(on)}	V _{GS} =2.5V, I _D =3.5A			45	
Forward transconductance	g FS	V _{DS} =5V, I _D =7A	9			S
Diode forward voltage	V _{SD}	I _S =1.7A,V _{GS} =0V		0.7	1.3	V
Dynamic characteristics	•		•	•	•	
Total gate charge	Qg	V _{DS} =10V,V _{GS} =4.5V,I _D =4A		11		nC
Gate-source charge	Qgs			2.3		
Gate-drain charge	Q _{gd}			2.5		
Input Capacitance	C _{iss}			800		
Output Capacitance	Coss	V _{DS} =8V,V _{GS} =0V,f=1MHz		155		pF
Reverse Transfer Capacitance	C _{rss}			125		
Switching Characteristics	•					
Turn-on delay time	t _{d(on)}	V _{DD} =10V , V _{GS} =4V , I _D =1A		18		
Turn-on rise time	t _r			5		
Turn-off delay time	t _{d(off)}	$R_G=10\Omega$		43		ns -
Turn-off fall time	t _f			20		

Notes: 1. Pulse Test: Pulse width≤300µs, duty cycle≤0.5%.

2. Guaranteed by design, not subject to production testing.



Electrical characteristics - P-Channel Q2 (T_A=25 °C, unless otherwise noted)

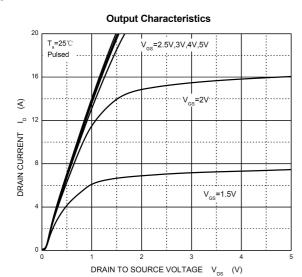
Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-16V,V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V_{DS} =VGS, I_D = -250 μ A	-0.5	-0.7	-1	V
Drain source on resistance	D	V _{GS} = -4.5V, I _D = -0.5A		70	90	<u> </u>
Drain-source on-resistance	R _{DS(on)}	V _{GS} = -2.5V, I _D = - 0.5A		90	110	
Forward transconductance	g FS	V_{DS} =-5V, I_{D} = -2A	5			S
Dynamic characteristics						
Input Capacitance	C _{iss}			405		
Output Capacitance	Coss	V _{DS} =-10V,V _{GS} =0V,f=1MHz		75		pF
Reverse Transfer Capacitance	C _{rss}			55		
Gate resistance	Rg	f=1MHz		6		Ω
Total Gate Charge	Qg			3.3	12	
Gate-Source Charge	Q _{gs}	V _{DS} =-10V,V _{GS} =-2.5V,ID=-3A		0.7		nC
Gate-Drain Charge	Q _{gd}			1.3		
Turn-on delay time	t _{d(on)}			11		
Turn-on rise time	tr	V _{DD} =-10V,V _{GEN} =-4.5V,I _D =-1A		35		
Turn-off delay time	t _{d(off)}	$R_L=10\Omega, R_{GEN}=1\Omega$		30		ns
Turn-off fall time	t _f			10		
Source-Drain Diode characteristics						
Diode Forward voltage	V _{DS}	V _{GS} =0V, I _S =-1.25A		-0.7	-1.3	V

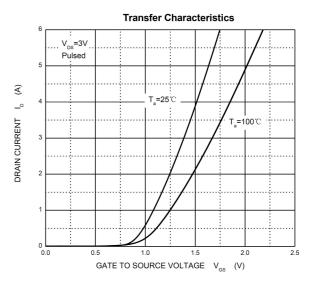
Notes: 1. Pulse Test: Pulse width≤300µs, duty cycle≤0.5%.

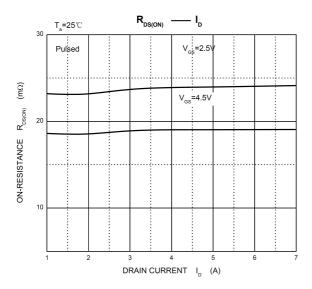
2. Guaranteed by design, not subject to production testing.

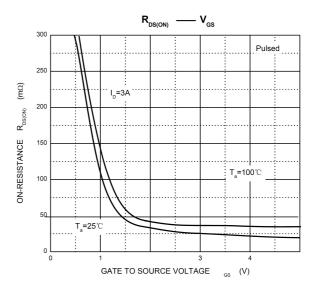


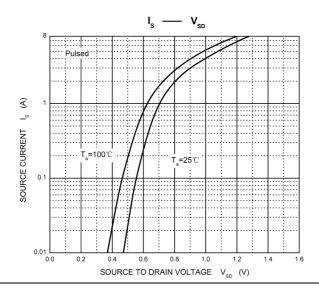
Typical Characteristics - N-Channel Q1

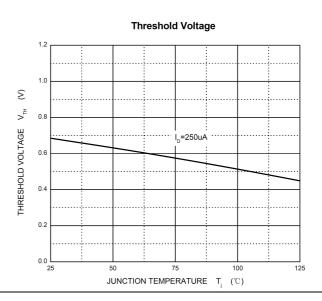






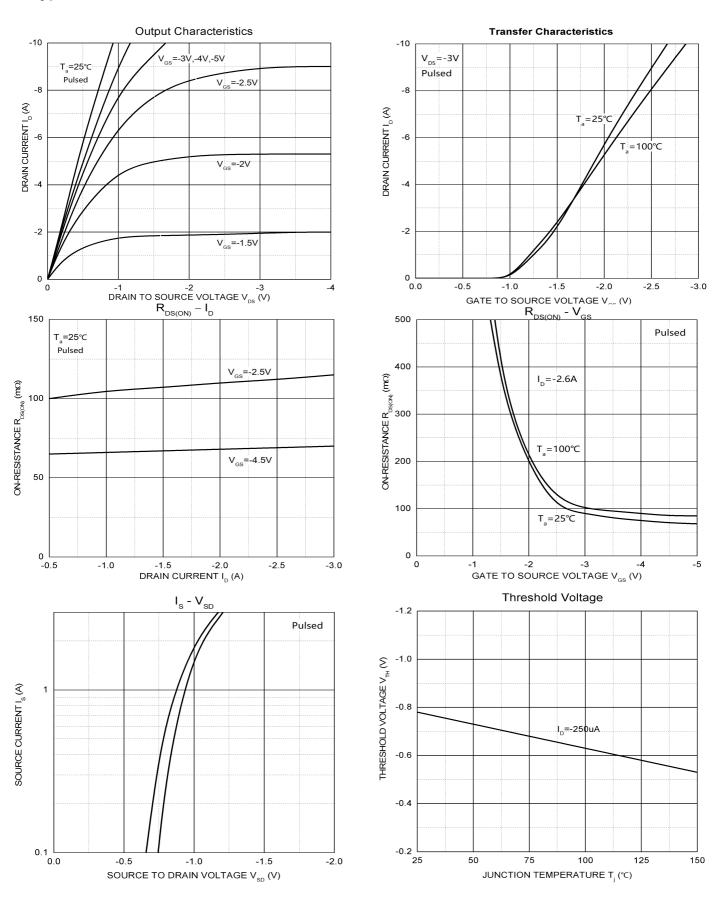








Typical Characteristics - P-Channel Q2





Ordering Information:

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

Note: Adding "-HF" suffix for halogen free, eg. Part Number-TP-HF

IMPORTANT NOTICE

Micro Commercial Components Corp. reserves the right to make changes without further notice to any product herein to make corrections, modifications, enhancements, improvements, or other changes. **Micro Commercial Components Corp.** does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold **Micro Commercial Components Corp.** and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

MCC's products are not authorized for use as critical components in life support devices or systems without the express written approval of Micro Commercial Components Corporation.

CUSTOMER AWARENESS

Counterfeiting of semiconductor parts is a growing problem in the industry. Micro Commercial Components (MCC) is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. MCC strongly encourages customers to purchase MCC parts either directly from MCC or from Authorized MCC Distributors who are listed by country on our web page cited below. Products customers buy either from MCC directly or from Authorized MCC Distributors are genuine parts, have full traceability, meet MCC's quality standards for handling and storage. MCC will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. MCC is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.